

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	5401	438/301.ccls. 438/303.ccls. 438/675.ccls. 438/786.ccls. 438/791.ccls. 427/249.15.ccls. 427/255.27.ccls. 427/255.28.ccls. 427/255.393.ccls. 427/255.394. ccls.	US-PGPUB; USPAT	OR	OFF	2006/08/25 14:12
L3	175	L2 and (hydrazine azido)	US-PGPUB; USPAT	OR	ON	2006/08/25 14:12
L4	0	L3 and (sin sicn siocn oxynitride nitride carbonitride)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:12
L5	9384	btbas ((bis tertiary butyl amino butylamino) near4 silane)	US-PGPUB; USPAT	OR	ON	2006/08/25 14:12
L6	5401	438/301.ccls. 438/303.ccls. 438/675.ccls. 438/786.ccls. 438/791.ccls. 427/249.15.ccls. 427/255.27.ccls. 427/255.28.ccls. 427/255.393.ccls. 427/255.394. ccls.	US-PGPUB; USPAT	OR	OFF	2006/08/25 14:12
L7	75	L5 and L6	US-PGPUB; USPAT	OR	ON	2006/08/25 14:12
L8	282	L5 same (sin sicn siocn oxynitride nitride carbonitride)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:16
L9	175	L6 and (hydrazine azido)	US-PGPUB; USPAT	OR	ON	2006/08/25 14:50
L10	3766	btbas ((bis tertiary butyl amino butylamino) near4 silane)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:55
L11	79	L10 and (sin sicn siocn oxynitride nitride carbonitride)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:55
L12	734	(pocket adj implant)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:00
L13	256	L12 same (source drain) same type	US-PGPUB; USPAT	OR	ON	2006/08/25 15:00
L14	18	L13 same (self adj align\$8)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:00
L15	38	(damascene inlaid "in-laid") same ((etchstop (etch\$6 near stop\$6)) with nitride) same (cmos nmos pmos mosfet fet transistor)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:01
L16	1152	(spacer sidewall (side adj wall)) near2 sacrificial	US-PGPUB; USPAT	OR	ON	2006/08/25 15:03

## EAST Search History

L17	13	L16 same ((heav\$6 near2 (doped implant\$6)) with first)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:03
L18	57	L16 and (438/301.ccls. 438/303. ccls. 438/675.ccls. 438/786.ccls. 438/791.ccls. 427/249.15.ccls. 427/255.27.ccls. 427/255.28.ccls. 427/255.393.ccls. 427/255.394. ccls.)	US-PGPUB; USPAT	OR	ON	2006/08/25 15:05
L19	374	438/786.ccls.	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:06
L20	1151	((sin sicn "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride carbonitride) and ((silicon si) with (nitrogen "n. sub.2"))).clm.	US-PGPUB	OR	ON	2006/08/25 15:18
L21	431	((sin sicn "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride carbonitride) and ((silicon si) with (nitrogen "n. sub.2")) and ((semiconductor adj device) integrated circuit)).clm.	US-PGPUB	OR	ON	2006/08/25 15:19
L22	123	((sin sicn "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride carbonitride) and ((silicon si) with (nitrogen "n. sub.2")) and ((semiconductor adj device) integrated circuit) and (compound ((raw source) adj (material gas)) precursor hydrazine azido btbas ((bis tertiary butyl amino butylamino) near4 silane))).clm.	US-PGPUB	OR	ON	2006/08/25 15:23